BORN SEMICONDUCTOR

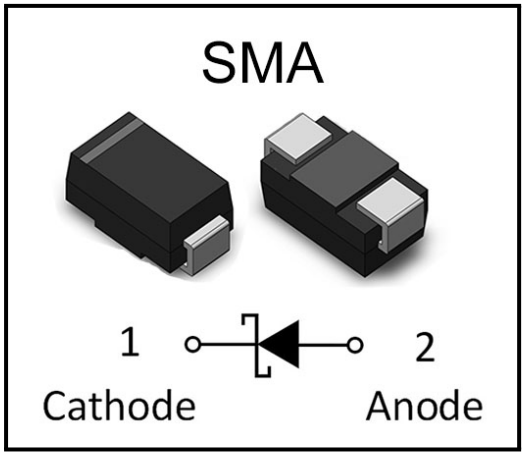
SS32-SS320

Schottky Barrier Diode

Features

- For surface mounted applications
- Matal silicon junction,majority carrier conduction
- Low power loss,high efficiency
- Buit-in strain relief,ideal for automated placement
- High forward surge current capability
- High temperature soldering guaranteed: 250°C/10 seconds at terminals

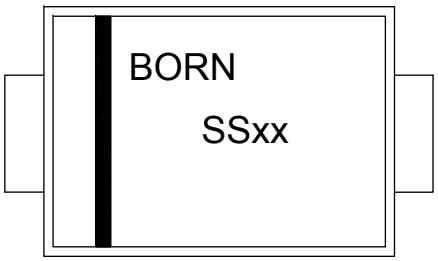
Package



Description

- Case: JEDEC DO-214AC molded plastic
- Terminals:Axial leads.Solderable per MIL-STD-750 Method 2026
- Polarity: Color band denotes cathode
- Mounting Position:Any

Marking



Ordering information

Part Number	SS32	SS33	SS34	SS35	SS36	SS38	SS39	SS310	SS315	SS320
Marking	SS32	SS33	SS34	SS35	SS36	SS38	SS39	SS310	SS315	SS320
Base qty	5K	5K	5K	5K	5K	5K	5K	5K	5K	5K

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SS32-SS320

Schottky Barrier Diode

Maximum Ratings and Electrical Characteristics@T_A=25°C unless otherwise noted

Symbol	Parameters	SS 32	SS 33	SS 34	SS 35	SS 36	SS 38	SS 39	SS 310	SS 315	SS 320	Units
V_{RRM}	Maximum Repetitive Peak Reverse Voltage	20	30	40	50	60	80	90	100	150	200	V
$V_{R(RMS)}$	Maximum RMS Reverse Voltage	14	21	28	35	42	56	63	70	105	140	V
V_{DC}	Maximum DC Blocking Voltage	20	30	40	50	60	80	90	100	150	200	V
$I_{F(AV)}$	Max. average forward Rectified Current	3.0										A
I_{FSM}	Non-repetitive peak forward surge current 8.3 ms singlehalf sine-wave	80										A
V_F	Maximum Instantaneous Forward Voltage @I_F=3.0A	0.55			0.70		0.85			0.95		V
I_R	Peak Reverse current at T_A=25°C	0.50					0.10					mA
	Rated DC Blocking Voltage T_A=100°C	10					5.0					
T_J	Operating Temperature Range	-55 to +150										°C
T_{STG}	Storage Temperature Range	-55 to +150										°C
$R_{\theta JA}$	Thermal Resistance(1)	55										°C/W
$R_{\theta JL}$		17										

Note:(1)Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B.with 0.2” x 0.2” (5.0 mm x 5.0 mm)copper pad areas.

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SS32-SS320

Schottky Barrier Diode

Typical Performance Characteristics(T_J = 25 °C, unless otherwise noted)

Figure 1:I_O-T_L Curve

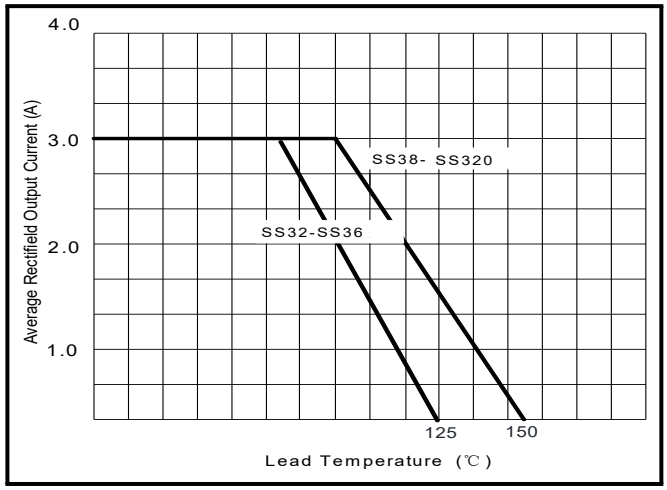


Figure 2:Surge Forward Current Capability

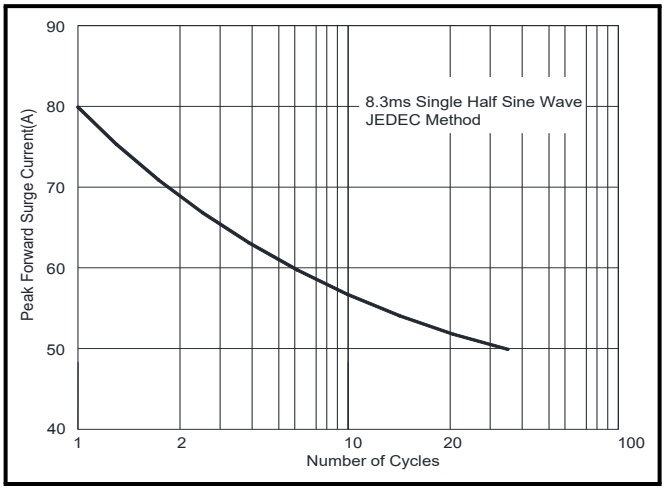


Figure 3:Typical Forward Characteristics

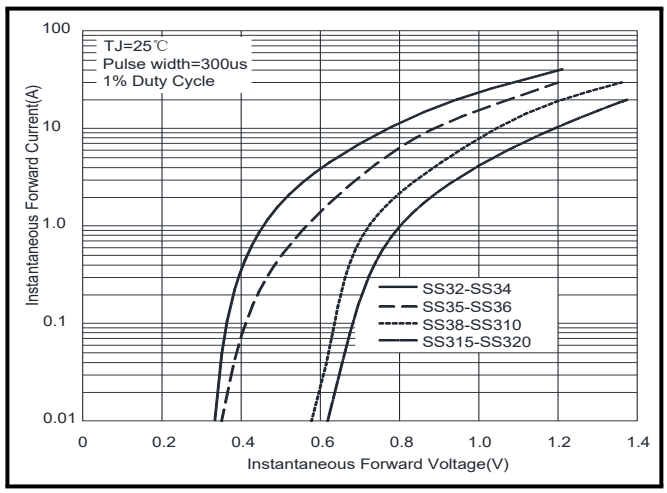
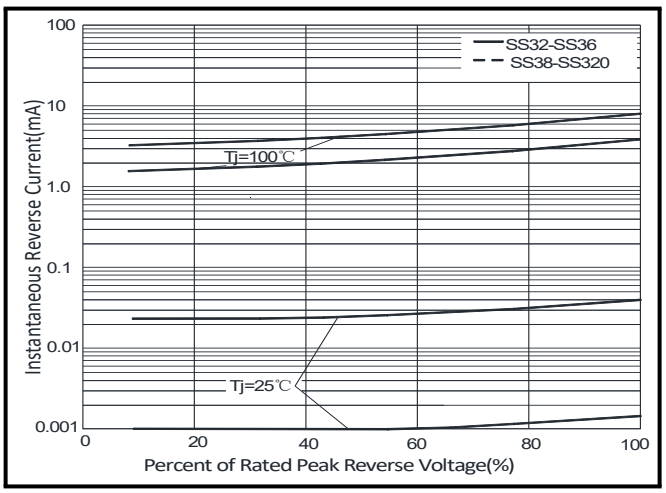


Figure 4: Typical Reverse Characteristics



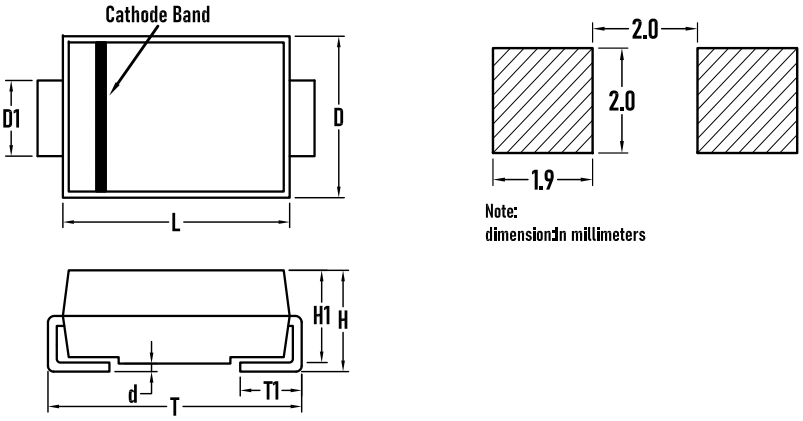
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SS32-SS320

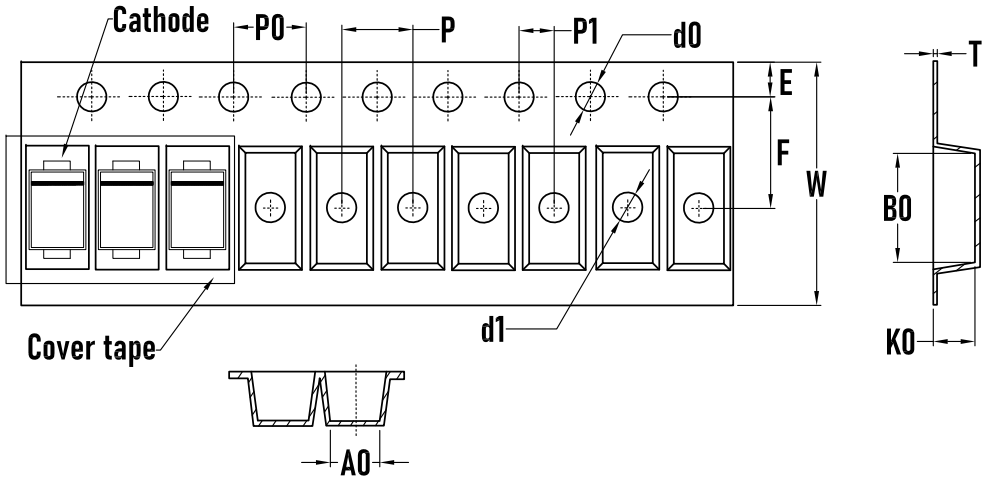
Schottky Barrier Diode

Outline Drawing - SMA



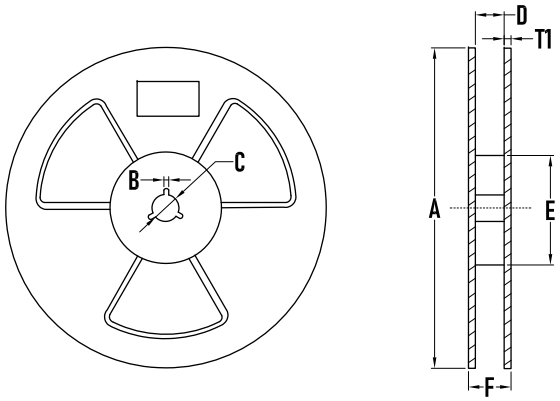
SYMBOL	MILLIMETER		Inches	
	MIN.	MAX.	MIN.	MAX.
D	2.5	2.9	0.098	0.114
D1	1.2	1.8	0.047	0.071
T	4.8	5.3	0.189	0.209
T1	0.8	1.5	0.031	0.059
d	–	0.2	–	0.008
H1	1.8	2.2	0.071	0.087
H	1.9	2.5	0.075	0.098
L	3.9	4.6	0.154	0.181

Packaging Tape - SMA



SYMBOL	MILLIMETER
A0	2.70
B0	5.10±0.1
d0	1.50±0.1
d1	1.50±0.1
E	1.75±0.1
F	5.50±0.1
K0	2.40±0.1
P	4.00±0.1
P0	4.00±0.1
P1	2.00±0.1
W	12.00±0.1
T	0.2±0.02

Packaging Reel



SYMBOL	MILLIMETER
A	323±2
B	3.0±0.2
C	15.0±0.5
D	13±2
E	73±2
T1	2.2±0.2
Quantity	5000PCS

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